



5082-0008

STEP RECOVERY DIODE CHIP

DESCRIPTION:

The **ASI 5082-0008** is a Silicon Oxide Passivated SRD Chip Designed for hybrid local oscillator Applications.

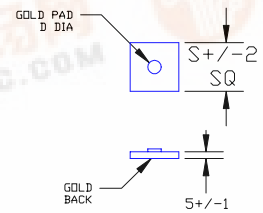
FEATURES:

- Gold contact metalization
- Passivated Chip

MAXIMUM RATINGS

| | |
|-------------------------|---------------------------------|
| I | 100 mA |
| V | 15 V |
| P_{DISS} | 100 mW @ T _C = 25 °C |
| T_J | -60 °C to +200 °C |
| T_{STG} | -65 °C to +200 °C |
| T_{SOLD} | t ≤ 1.0 MINUTE +310 °C |

PACKAGE STYLE CHIP



| CHIP SIZE CODE X | CHIP SIZE Y | PAD SIZE CODE | PAD DIA |
|------------------|-------------|---------------|---------|
| 1 | 15 | 1 | 1T02 |
| 2 | 20 | 2 | ≥2 |
| 3 | 30 | | |
| 7 | 70 | | |
| | | | |
| | | | |

CHIP = 0.020 X 0.020 X 0.011 INCHES
 TOP BOND CONTACT GOLD = 0.0025 INCHES
 BOTTOM CONTACT GOLD (FULL AREA)

CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|----------------------|---|---------|---------|---------|-------------|
| V_B | I _R = 10 μA | 15 | | | V |
| C_J | V _R = 10 V f = 1.0 MHz | | | 0.38 | pF |
| R_S | I _F = 20 mA f = 100 MHz | | 0.8 | | Ohms |
| τ | I _F = 10 mA I _R = 6.0 mA | | 10 | | μS |
| t_i | C _L = 100 pc | | 60 | | pS |

